

Index

3 dB bandwidth, 247, 252
active material, 7
active medium, 7, 132. *See* gain medium
 bulk, 7
 multiple quantum well, 7
 quantum dot, 7
 surface-to-volume ratio, 171
 volume, 134
adhesion layer, 160
aluminum nitride, 178
aluminum oxide, 154
amplified spontaneous emission, 62, 212
atomic layer deposition (ALD), 174,
 266
axial symmetric, 136
Bardeen-Cooper-Schrieffer (BCS), 221
Bessel function, 39, 292, 297
bit-error rate, 253
Bloch plasmon-polariton (BPP), 93
Bohr radius, 221
Bose-Einstein condensate, 214, 216
boundary-value problem, 43
Bragg period, 2
Bragg grating, 256, 257
bulk gain, 133, 135, 145, 249, 250
cavity
 linewidth, 73, 248
 mode, 13, 80
 transparent condition, 66, 73, 75
Cavity-free nanolaser, 26, 202
cavity-QED, 66, 312
CCD camera, 59, 61, 62, 160
chip-scale integration, vii, 3, 9, 30, 37, 54,
 119, 123, 132, 168, 231, 245, 256, 263,
 266, 317
clamp
 carrier, 144
 current, 171
clamping
 carrier, 142

cloud computing, 231
CMOS compatible, 54, 118, 233, 234
coherence, 10, 63, 89, 261
 first order. *See* spatial coherence
 phase, 212
 spatial, 59, 62, 63, 227
colloidal QD, 9
composite gain waveguide, 38
confinement factor, 6, 11, 16, 18, 21, 72
 energy confinement factor, 13
 power confinement factor, 13
 power confinement factor, electric field
 confinement factor, electric energy confinement
 factor, 16
constriction resistance, 200, 292
core-shell, 23, 26, 99
coupling coefficient, 257
coupling efficiency, 131, 239, 263
current crowding, 200, 292
cutoff frequency, 127
data transmission, 93, 231, 232
data-rate ratio, 254
density of states
 electronic, 6, 136, 138, 223, 279
 free space, 114
 photonic, 6, 212
 reduced, 67
dielectric constant, 120, 203
diffraction limit, 10, 29, 93
diffusion, 55, 58, 138, 139
 length, 71
 time, 71
direct-transition model, 67
dispersion relation, 27, 39, 203, 265
 k-point, 27, 202
distributed Bragg reflector, 20, 219
double heterostructure, 99, 133, 148,
 159, 162
drift, 138, 261
Drude model, 81, 92, 191
dry etch, 58, 160, 165, 200
 reactive ion etching, 51

- e-beam evaporation, 160
- e-beam lithography, 58, 123, 159, 178
- edge-emitting, 235, 261
- effective index, 10, 92, 98, 157
 - mismatch, 157
- effective mass, 218, 278
 - reduced, 279
- effective medium theory, 98, 265
- effective mode volume, 3, 16
- electrical insulation, 37, 147, 162, 177, 178, 246
- electro-luminescence, 31, 162
- emitter-field-reservoir model, 66
- energy confinement factor. *See* confinement factor
- epitaxial, 25, 177, 227, 235, 259
- epitaxially grown, 9, 57
- evanescent, 127, 235, 242
- evanescent-coupling, 242
- exciton-polariton laser, 10, 215
 - inversionless laser, 133
- excitons, 133, 215, 216, 221
- Fabry-Perot cavity, 10, 12, 21, 22, 29, 146, 165
- Fermi distribution, 75, 253
- field antinode, 71, 227
- field node, 71, 274
- finite element method (FEM), 41
- finite-difference time-domain (FDTD), 98
- footprint, 3, 29, 30, 149, 192, 235, 263
- full-width-at-half-maximum (FWHM), 66, 70, 72, 75, 219
- gain
 - bandwidth, 103, 197
 - spectrum, 8, 67, 68, 85, 275, 279
 - temperature dependence of, 275, 279
- gain coefficient, 37, 246
- gain medium, 67
- Gaussian lineshape, 207, 208, 238, 248
- group velocity, 27, 100, 141, 202, 210, 211
- Hamiltonian, 69, 270
- heat capacity, 176
- heterogeneous integration, 235
- high speed optical communication, 245
- hybrid mode, 32
- hyperbolic metamaterial, 98, 264
- III-V/Si, 235, 256
- inorganic semiconductor, 8
- Internet of Things, 231
- inversionless laser
 - exciton-polariton laser, 214
- Langevin, 255, 271
- large-signal modulation, 253
- lasing threshold, 2, 14, 18
- L-I* curve, 161, 162, 164, 250
- lifetime
 - Auger recombination, 114, 116, 289
 - carrier, 68, 288
 - intraband, 280
 - non-radiative recombination, 14, 16, 114, 116, 141
 - photon, 16, 17, 20
 - spontaneous emission, 83, 99
 - surface recombination, 114, 116, 141, 195, 288
- light emitting device, 14
- light-light curve, 18, 97, 116
 - S-shape, 108, 211
- light-matter interaction, 22, 132
- lineshape
 - broadening of, 67, 72, 280
 - cavity, 67
 - Lorentzian, 70, 72, 75, 111
- LL curve. *See* light-light curve
- localized surface plasmon (LSP), 93
- longitudinal mode, 130, 137, 138, 258
- long-range SPP, 96
- lossless propagation, 5, 36, 38, 98, 265
- lower polariton, 216, 224
- magnetic-dipole-like mode, 122
- material dispersion, 18, 100, 146
- matrix element, 84
 - dipole, 70, 71, 273
 - momentum, 67
 - transition, 275
- membrane, 1, 177, 178, 269
- metal sputtering, 29, 53, 58
- metal-cladding, 12, 59, 146, 165, 236, 240, 267
 - metallo-dielectric, 42, 56, 114
- metal-dielectric interface, 5, 32
- metal-dielectric-metal (MDM), 28
- metal-insulator-metal. *See* metal-dielectric-metal
- metal-semiconductor-metal. *See* metal-dielectric-metal
- micro-photoluminescence, 59
- microscale
 - heat-transfer, 176
 - laser, 19, 256
- microscope objective, 60
- mirofluidic and/or optofluidic, 9
- modal dispersion, 203, 207, 210, 211
- modal gain, 8, 11, 12, 13, 29, 171
- mode spacing, 100
- mode-gain overlap, 3, 8, 73
- modulation bandwidth, 1, 245, 254, 255
- modulation speed, 73, 118, 231, 245–255
- monochromator, 61, 224, 258
- MQW gain, 8, 51, 72, 90, 133, 138, 143, 145, 249, 250
- multi-physics design, 146, 168, 200
- nano-antenna, 31, 35
- nanoLED, 245, 246, 249

- nanowire, 22
- near-infrared, 27, 50, 93, 124, 205
- noble metal, 118, 265
- normalized mode volume, 249
- numerical aperture, 117, 125
- optical communication, 37, 56, 65, 94, 269
- optical interconnects, 132, 166, 232
- organic semiconductor, 9
- passivation, 177
 - layer, 147, 178, 189
 - material, 178
 - surface, 162, 176
- patch antenna, 119, 120
- PECVD, 51, 160, 177, 178
- photoluminescence, 62
- photon density, 17, 18, 245, 253
- photonic bandgap, 21, 117
- photonic crystal defect laser, 21
- photonic crystal laser, 21, 177, 267
 - broad-area cavity, 21
 - defect cavity, 21
- photonic integrated circuit, 9, 259
- photonic mode, 28, 34, 36, 117
- photoresist planarization, 160
- planar integration, 135
- plasma frequency, 31, 81, 98, 119, 203
- plasma-enhanced ALD, 178
- plasmonic mode, 6, 93, 97, 117
- polaritons, 216, 217, 221, 225, 228
- population inversion, 10, 97, 214, 215, 224
- power consumption, 2, 132, 133, 231, 232, 245, 252, 261, 263, 267
- power-to-bandwidth ratio (PBR), 252
- Poynting vector, 96, 209, 212, 213
- propagation constant, 5, 28, 33, 43, 96, 204, 238, 257
- propagation loss, 5, 11, 91, 118, 260
- Purcell effect, 1, 15, 18, 65–67, 69–78, 98, 246
 - Purcell factor, 15, 65, 71–77, 78
 - spontaneous emission factor, 77
 - temperature dependence of, 78–80
- Q factor, 17, 70, 219, 264
- QD gain, 8, 21, 247, 251, 253
- quantization volume, 270
- quantum efficiency, 14, 139, 261
 - external, 14
 - internal, 14
- quantum yield
 - quantum efficiency, 14
- quasi-Fermi level, 68, 142
 - electron, 134
 - hole, 134
- radiation loss, 6, 12, 32, 38, 73, 80, 101, 120, 128
- Raman laser, 54, 234
- reflection coefficient, 146, 157
- refractive index units, 64
- resistor-capacitor, 1
- scalability, 101, 231, 235
- scanning electron microscope, 58
- Scanning Transmission Electron Microscopy (STEM), 25
- sidewall tilt, 150, 169, 173, 291, 293
- silicon dioxide, 26
- silicon laser, 263
- silicon photonics, 56, 233, 256
- small-signal analysis, 210, 252
- small-signal modulation, vii, 245
- SPASER, 34
- spectral density, 144, 212, 254, 255
- spectrometer, 61, 224
- spontaneous emission
 - lifetime, 114. *See* spontaneous emission rate
 - modification. *See* Purcell effect
 - rate, 15, 17, 65, 87, 114
 - spectrum, 84
 - temperature dependence of, 78–88
- spontaneous emission rate
 - enhancement, 65
 - inhibition, 65, 143
- spot size, 60, 235
- steady-state, 70, 173, 176, 194, 211, 212, 244
- strong coupling, 93, 214, 221, 229
- Super-luminescent Light Emitting Diode (SLED), 59
- surface roughness, 24, 159, 178, 200, 207
- surface-emitting, 264
- surface-enhanced Raman spectroscopy (SERS), 93
- TE polarization, 100, 121, 125, 238, 279
- temperature effect
 - cavity modes, 80–84
 - insensitivity of spontaneous emission factor, 88–90
 - spontaneous emission, 80–84
 - spontaneous emission factor, 78–88
- temporal coherence, 33
- thermal conductivity, 169, 174, 176, 187, 200
- thermal equilibrium, 141, 216, 223, 275
- thermal reservoir, 69, 74, 272
- thresholdless, 1, 18, 32, 65, 264
- TM polarization, 98, 120, 279
- total internal reflection, 32
- total optical energy confinement factor. *See* energy confinement factor
- transfer matrix method, 39, 98, 204, 219, 220
- transient, 93, 107, 173, 211
- transmission coefficient, 146
- transparent conducting oxides (TCO), 265, 266
 - indium tin oxide (ITO), 205

- transparent propagation, 5, 94
transverse electromagnetic (TEM), 96, 102, 103, 109
transverse mode, 21
two-level system, 66, 270, 272
- undercut, 130, 135, 149, 169
 ratio, 153, 169, 192
upper polariton, 216, 220
- vacuum wavelength, 41, 211
- Vertical cavity surface-emitting laser (VCSEL), 19
- volume plasmon-polariton (VPP). *See* Bloch
 plasmon-polariton (BPP)
- wafer bonding, 54, 235
 plasma-assisted, 235, 257
wall-plug efficiency, 14, 235
waveguide coupling, 235, 239, 242, 244, 259
wavelength division multiplexing, 133, 232
weak coupling regime, 74, 79, 215, 219, 220, 230, 272, 273
wet etch, 123, 152, 160, 178
whispering gallery mode, 31, 97, 123, 157, 268
zero temperature condition, 69